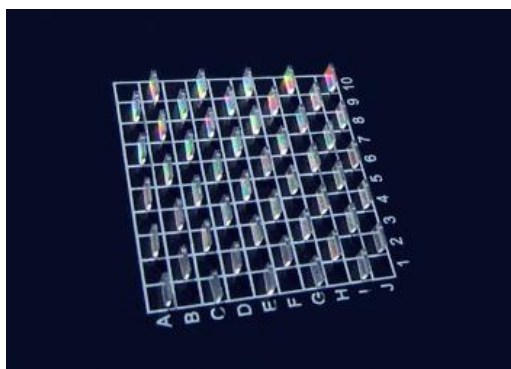


Mgo:PPLN Crystals Chips for 532nm Laser Generation

without OC Mirrors

- High power and high efficiency
- Small size, no mirrors needed

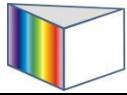
The MgO doped periodically poled lithium niobate chips (or **PPLN crystals**) for 532nm laser generation with high-power up to 4 watts are offered in Hangzhou Shalom EO, the output facet is coated with HR@1064nm and HT@532nm, it makes the OC mirrors unnecessary for your lasers, which may reduce the cost and the size of your laser system.



SPECIFICATIONS

Optical Specification	
Length	1.0~2.0mm
Width	~ 2.0mm
Thickness	0.5mm
Coating on Input facet	AR@1064nm + AR @532nm
Coating on Output facet	HR@1064nm + HT@532nm (without output mirror)
Optical to Optical Efficiency (intra-cavity)	³ 30%
Operation Temperature	~ 33° C
Temperature Tolerance	> 25 °C

Note: The PPLN crystals with the Copper heat-sink packing is available.



Polishing Specifications	
Tolerance of Size	(Width±0.1mm) x(Thickness±0.05mm) X (Length±0.1mm)
Flatness	< Lambda/8 @ 633nm
Wavefront Distortion	< Lambda/6 @ 633nm
Chips	<0.1mm
Surface Quality	20/10 S/D
Parallelism	<10"
Perpendicularity	<10'

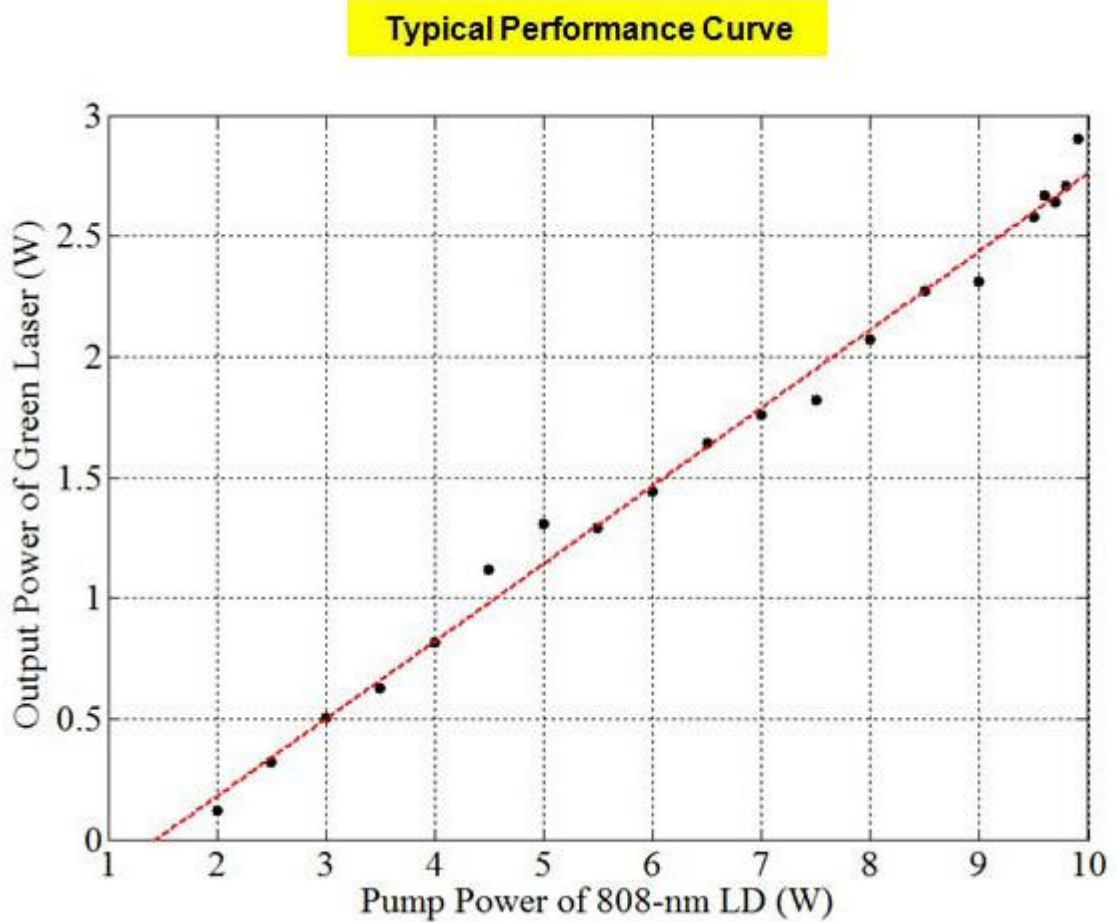
Basic Properties

Chemical and Physical Properties	
Melting Point	1255+/-5 °C
Curie Point/Temperature	1140+/-5 °C
Mohs Hardness	5
Density	4.648(5)g/cm ³
Thermal conductivity	38W/m/K @ 25 °C
Coefficient of thermal expansion	//a, 2.0x10 ⁻⁶ /K //c, 2.2x10 ⁻⁶ /K

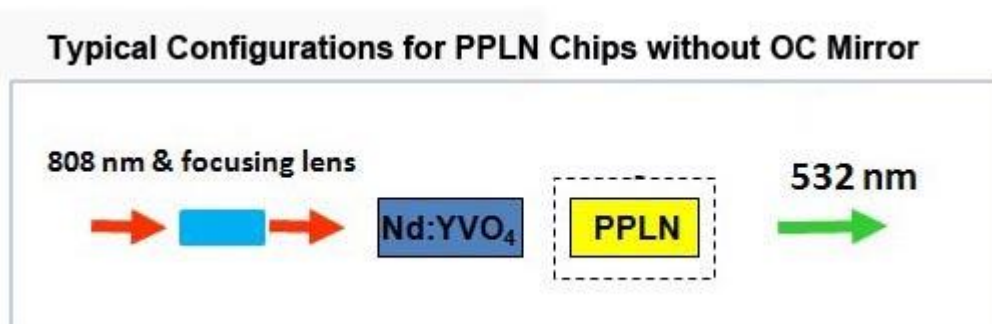
Optical and Nonlinear properties	
Wavelength range of Transmission	420nm ~ 5200nm
Nonlinear coefficient	d ₃₃ = 34.4 pm/V d ₃₁ = d ₁₅ = 5.95 pm/V d ₂₂ = 3.07 pm/V
Optical Damaging Threshold	0.3GW/cm ²
Absorptive Coefficient	0.004/cm @ 1064nm

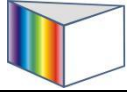
Application Notes

Typical Performance Curve



Typical Configurations for PPLN chips without OCMirror





Shalom EO
Crystals, optics and components

Hangzhou Shalom Electro-optics Technology Co., Ltd.
